IN THE CLAIMS:

Please amend claims 1-26 as follows:

Claim 1 (Currently Amended): An electroluminescent device comprising:

a substrate having a smooth surface;

a lower electrode layer ~~over~~ having a first surface in contact with the smooth surface of the substrate~~, having~~ and a second surface with a plurality of convex shapes ~~in it's surface~~;

an insulating layer over the lower electrode layer;

a light-emitting layer over the insulating layer;

an upper electrode layer ~~over~~ formed directly on the light-emitting layer; and

a passivation layer over the upper electrode layer,

wherein the insulating layer, the light-emitting layer, and the upper electrode layer are formed in succession.

A1

Claim 2 (Original): The electroluminescent device according to claim 1, wherein the lower electrode layer has a layered structure including a polysilicon layer and a metal layer.

Claim 3 (Original): The electroluminescent device according to claim 2, wherein the polysilicon layer has a plurality of convex shapes in its surface.

Claim 4 (Original): The electroluminescent device according to claim 2, wherein the metal layer includes at least one of Al and Ag.

Claim 5 (Original): The electroluminescent device according to claim 1, wherein the lower electrode layer has a layered structure including a tungsten layer and a metal layer.

A1 cont.

Claim 6 (Original): The electroluminescent device according to claim 5, wherein the tungsten layer has a plurality of convex shapes in its surface.

Claim 7 (Original): The electroluminescent device according to claim 5, wherein the metal layer includes at least one of Al and Ag.

Claim 8 (Original): The electroluminescent device according to claim 1, wherein the insulating layer, the light-emitting layer, and the upper electrode layer have substantially the same surface profile as the lower electrode layer.

Claim 9 (Original): The electroluminescent device according to claim 1, wherein the lower electrode layer has a single layer structure of a metal layer.

Claim 10 (Original): The electroluminescent device according to claim 9, wherein the metal layer includes at least one of Al and Ag.

Claim 11 (Original): The electroluminescent device according to claim 1, wherein the insulating layer includes $BaTiO_3$.

Claim 12 (Original): The electroluminescent device according to claim 1, wherein the upper electrode layer includes indium tin oxide (ITO).

Claim 13 (Original): The electroluminescent device according to claim 1, wherein the light-emitting layer includes ZnS doped with at least one of Cu and Mn.

Claim 14 (Withdrawn): A method for manufacturing an electroluminescent device, the method comprising:

forming, over a substrate, a lower electrode layer having a plurality of convex shapes in its surface;

forming, over the lower electrode layer, an insulating layer, a light-emitting layer, and an upper electrode layer in succession so that the insulating layer, the light-emitting layer, and the upper electrode layer have substantially the same surface profile as the lower electrode layer; and

forming a passivation layer over the upper electrode layer.

Claim 15 (Withdrawn): The method according to claim 14, wherein forming the lower electrode layer includes:

forming, over the substrate, a polysilicon layer having a plurality of convex shapes in its surface; and

forming, over the polysilicon layer, a metal layer having substantially the same surface profile as the polysilicon layer.

A1 cont.

Claim 16 (Withdrawn): The method according to claim 15, wherein the polysilicon layer is formed by low pressure chemical vapor deposition (LPCVD) at a temperature between about 560°C and about 610°C.

Claim 17 (Withdrawn): The method according to claim 14, wherein forming the lower electrode layer includes:

forming, over the substrate, a tungsten layer having a plurality of convex shapes in its surface; and

forming, over the tungsten layer, a metal layer having substantially the same surface profile as the tungsten layer.

Claim 18 (Withdrawn): The method according to claim 17, wherein the tungsten layer is formed by chemical vapor deposition (CVD).

Claim 19 (Withdrawn): The method according to claim 14, wherein forming the lower electrode layer includes:

forming a metal layer over the substrate; and

A' cont

etching a surface of the metal layer to form a plurality of convex shapes thereon.

Claim 20 (Withdrawn): The method according to claim 19, wherein the metal layer is formed by thermal deposition.

Claim 21 (Withdrawn): The method according to claim 19, wherein etching the surface of the metal layer includes performing at least one of wet etching and dry etching.

Claim 22 (Withdrawn): The method according to claim 14, wherein forming the insulating layer includes forming a $BaTiO_3$ based material.

Claim 23 (Withdrawn): The method according to claim 14, wherein forming the light-emitting layer includes performing at least one of electron beam deposition and sputtering.

Claim 24 (Withdrawn): The method according to claim 14, wherein forming the upper electrode layer includes;

forming an indium tin oxide (ITO) layer; and

patterning the indium thin oxide layer.

A1 cancel.

Claim 25 (Currently Amended): An electroluminescent device comprising:

a substrate having a smooth surface

a lower electrode layer ~~over~~ having a first surface in contact with the smooth surface of the substrate~~, having~~ and a second surface with an uneven surface profile;

an insulating layer over the lower electrode layer, having an uneven surface profile substantially corresponding to the uneven surface profile of the lower electrode layer;

a light-emitting layer over the insulating layer, having an uneven surface profile substantially corresponding to the uneven surface profile of the insulating layer; and

an upper electrode layer ~~over~~ formed directly on the light-emitting layer, having an uneven surface profile substantially corresponding to the uneven surface profile of the light-emitting layer.

Claim 26 (Original): The electroluminescent device according to claim 1, wherein the uneven surface profile of the lower electrode has a plurality of convex shapes each of which is substantially hemispheric.